

Title (en)

N-TYPE METAL OXIDE SEMICONDUCTOR SPECTRALLY SENSITIZED WITH A CATIONIC SPECTRAL SENSITIZER

Title (de)

MIT EINEM KATIONISCHEN FARBSTOFF SPEKTRAL SENSIBILISIERTER N-METLLOXIDHALBLEITER

Title (fr)

SEMI-CONDUCTEUR A OXYDE METALLIQUE DE TYPE N SPECTRALEMENT SENSIBILISE PAR UN SENSIBILISATEUR SPECTRAL CATIONIQUE

Publication

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Application

EP 02772296 A 20020912

Priority

EP 0210269 W 20020912

Abstract (en)

[origin: WO2004025674A1] A layer configuration comprising a layer of a nano-porous n-type metal oxide semiconductor with a band-gap of greater than 2.7 eV, an adsorbed cationic spectral sensitizer and a coadsorber capable of enhancing the adsorption of a cationic spectral sensitizer on an n-type metal oxide semiconductor; and a process for preparing this layer configuration comprising the steps of: providing a layer of a nano-porous n-type metal oxide semiconductor with a band-gap of greater than 2.7 eV, adsorbing a coadsorber on the nano-porous n-type metal oxide semiconductor layer and adsorbing a cationic spectral sensitizer on the nano-porous n-type metal oxide semiconductor layer.

IPC 1-7

H01G 9/20

IPC 8 full level

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CPC (source: EP)

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Citation (examination)

- EP 0333641 A1 19890920 - SULZER AG [CH]
- H. TRIBUTSH, BER. BUNSENGES., vol. 73, no. 6, 1969, pages 582 - 590
- See also references of WO 2004025674A1

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